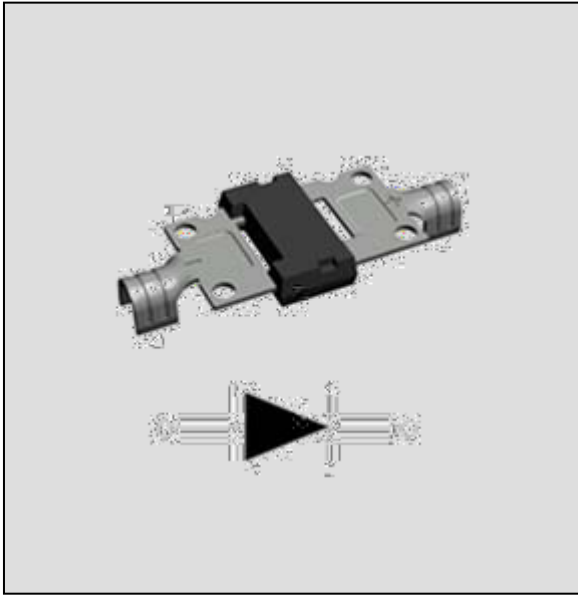




GFMK4045

Schottky Bypass Diode Module



Features

- High frequency operation
 - Low forward voltage drop
 - High purity, high temperature epoxy encapsulation for enhanced mechanical strength
- ØM r T marked

■Maximum Ratings (Ta=25 Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	GFMK4045
Device marking code			GFMK4045
Repetitive Peak Reverse Voltage	VRRM	V	45
Average Rectified Output Current @60Hz sine wave, R-load, Ta=25 -	IO	A	40
Surge(Non-repetitive)Forward Current @60Hz sine wave, 1 cycle, Tj=25 -	IFSM	A	400
Current Squared Time @1ms≤t<8.3ms Tj=25 - , Rating of per diode	I ² t	A ² S	660
Storage Temperature	Tstg	-	-55 ~+150
Junction Temperature IN DC Forward Mode-Forward Operations Èwithout reverse bias, t≤1 h (Fig. 1) Å1 Å	Tj	-	-55 ~+200

Note

(1) 12

Ta=100 -

IRRM3	mA	VRM=VRRM Ta=125 -	55



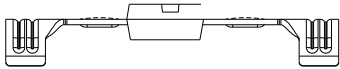
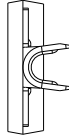
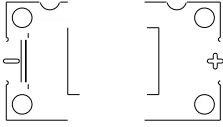
GFMK4045

■ Thermal Characteristics (T_a=25 Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	GFMK4045
Thermal Resistance θ_{JA}	R _{θJ-C}	- /W	1.5

*) 0.

v2XWOLQH 'LPHQVERQOLPHWHUV





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